



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

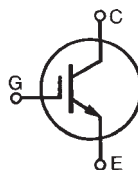
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



GenX3™ 300V IGBT IXGH60N30C3

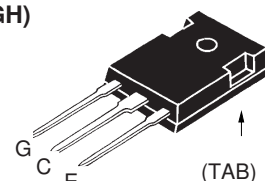
High Speed IGBTs for 50-150kHz switching



$$\begin{aligned} V_{CES} &= 300V \\ I_{C110} &= 60A \\ V_{CE(sat)} &\leq 1.8V \\ t_{fi \text{ typ}} &= 70ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	300	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GE} = 1M\Omega$	300	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Limited by leads)	75	A
I_{C110}	$T_C = 110^\circ\text{C}$ (chip capability)	60	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	420	A
I_A	$T_C = 25^\circ\text{C}$	60	A
E_{AS}	$T_C = 25^\circ\text{C}$	400	mJ
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 5\Omega$ Clamped inductive load @ $\leq 300V$	$I_{CM} = 170$	A
P_C	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062 in.) from case for 10s	260	$^\circ\text{C}$
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight		6	g

TO-247 AD
(IXGH)



G = Gate
E = Emitter
C = Collector
TAB = Collector

Features

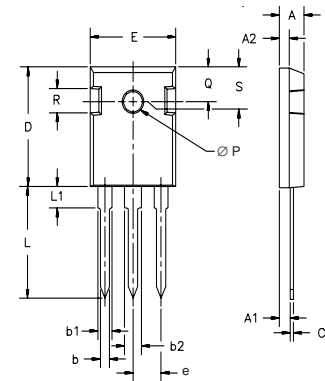
- High Frequency IGBT
- Square RBSOA
- High avalanche capability
- Drive simplicity with MOS Gate Turn-On
- High current handling capability

Applications

- PFC Circuits
- PDP Systems
- Switched-mode and resonant-mode converters and inverters
- SMPS
- AC motor speed control
- DC servo and robot drives
- DC choppers

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{GE} = 0V$	300		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	2.5		V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			30 μA 750 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 60A$, $V_{GE} = 15V$ $T_J = 125^\circ\text{C}$	1.55 1.60	1.8	V V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 0.5 \cdot I_{C110}$, $V_{CE} = 10\text{V}$ Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.	28	46	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		3800	pF
C_{oes}			240	pF
C_{res}			63	pF
Q_g	$I_C = I_{C110}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		101	nC
Q_{ge}			21	nC
Q_{gc}			37	nC
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ\text{C}$ $I_C = 0.5 \cdot I_{C110}$, $V_{GE} = 15\text{V}$ $V_{CE} = 200\text{V}$, $R_G = 5\Omega$		23	ns
t_{ri}			28	ns
E_{on}			0.15	mJ
$t_{d(off)}$			108	ns
t_{fi}			68	ns
E_{off}			0.30	0.55 mJ
$t_{d(on)}$	Inductive Load, $T_J = 125^\circ\text{C}$ $I_C = 0.5 \cdot I_{C110}$, $V_{GE} = 15\text{V}$ $V_{CE} = 200\text{V}$, $R_G = 5\Omega$		22	ns
t_{ri}			28	ns
E_{on}			0.26	mJ
$t_{d(off)}$			120	ns
t_{fi}			101	ns
E_{off}			0.40	mJ
R_{thJC}				0.42 $^\circ\text{C/W}$
R_{thCK}		0.21		$^\circ\text{C/W}$

TO-247 AD Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	